Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- MLPAK33 package (3.3 x 3.3 mm footprint)

3. Applications

- · DC-to-DC converters
- · Battery management
- · Low-side load-switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	=	11.3	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I_D = 7.5 A; T_j = 25 °C		-	15	18	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 6.6 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	18	23	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



30 V, N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	D
2	S	source		
3	S	source		G (F)
4	G	gate	l h d	mbb076 S
5	D	drain		
6	D	drain		
7	D	drain	MLPAK33 (SOT8002-1)	
8	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
PXN018-30QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1					

7. Marking

Table 4. Marking codes

Type number	Marking code
PXN018-30QL	9AA

30 V, N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	11.3	Α
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	7.5	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	4.8	Α
		V _{GS} = 10 V; T _{sp} = 25 °C		-	19.2	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	66	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T _{amb} = 25 °C	[1]	-	1.7	W
		T _{sp} = 25 °C		-	10.9	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode		'			
Is	source current	T _{amb} = 25 °C	[1]	-	1.5	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

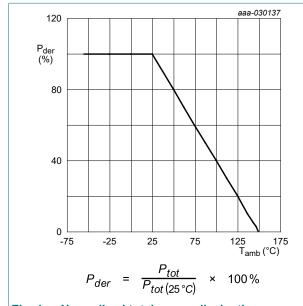


Fig. 1. Normalized total power dissipation as a function of ambient temperature

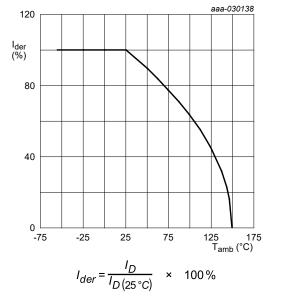


Fig. 2. Normalized continous drain current as a function of ambient temperature

30 V, N-channel Trench MOSFET

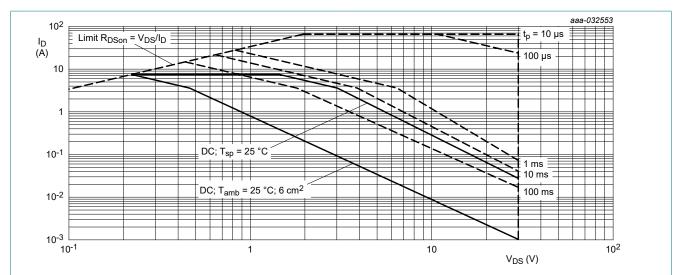


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

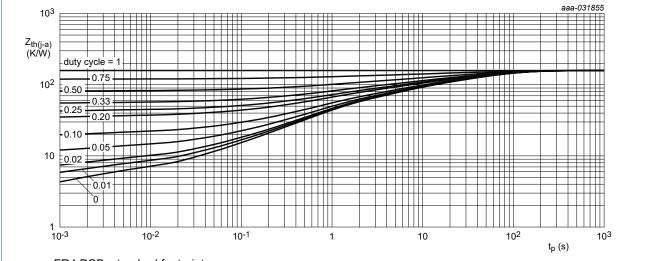
30 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
u i (j-a)	thermal resistance from	in free air	[1]	-	160	200	K/W
	junction to ambient		[2]	-	60	75	K/W
		in free air; t ≤ 5 s	[2]	-	28	33	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	8.3	11.5	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

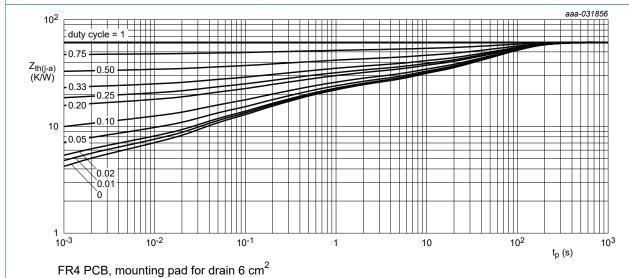


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.6	2.5	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.1	μΑ
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.1	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 7.5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	15	18	mΩ
	resistance	V _{GS} = 10 V; I _D = 7.5 A; T _j = 150 °C	-	25	30	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 6.6 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	18	23	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7.5 \text{ A}; T_j = 25 \text{ °C}$	-	25	-	S
R_{G}	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	naracteristics	•			<u> </u>	
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_D = 7.5 A; V_{GS} = 10 V; T_j = 25 °C	-	7.2	10.8	nC
		V _{DS} = 15 V; I _D = 6.6 A; V _{GS} = 4.5 V;	-	3.4	5.1	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.2	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	0.7	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge	_	-	0.5	-	nC
Q_{GD}	gate-drain charge		-	1	-	nC
V_{GSpl}	gate-source plateau voltage	V_{DS} = 15 V; I_D = 6.6 A; T_j = 25 °C	-	2.7	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	447	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	86	-	pF
C _{rss}	reverse transfer capacitance	-	-	30	-	pF
d(on)	turn-on delay time	V _{DS} = 15 V; I _D = 6.6 A; V _{GS} = 4.5 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	7	-	ns
t _{d(off)}	turn-off delay time	1	-	5	-	ns
t _f	fall time	1	-	2	-	ns
Source-drai	in diode		1			1
V _{SD}	source-drain voltage	I _S = 1.5 A; V _{GS} = 0 V; T _j = 25 °C	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_S = 1.5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	11	-	ns
Q _r	recovered charge	$V_{GS} = 4.5 \text{ V}; V_{DS} = 15 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	3	-	nC
t _a	reverse recovery rise time		-	7	-	ns
t _b	reverse recovery fall time		-	4	-	ns

30 V, N-channel Trench MOSFET

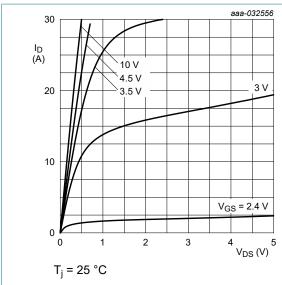


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

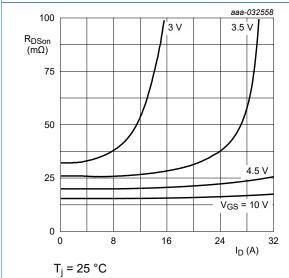


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

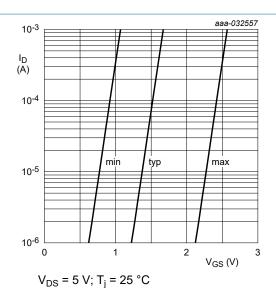


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

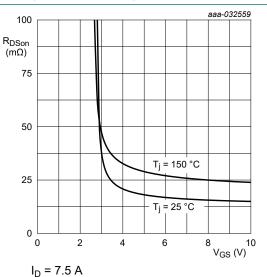


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

30 V, N-channel Trench MOSFET

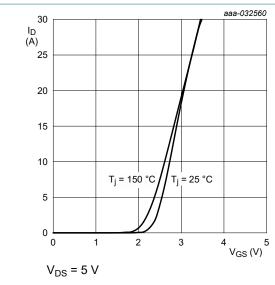


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

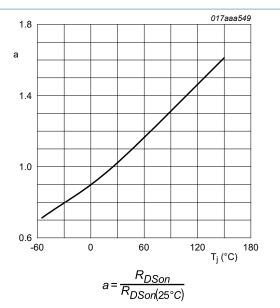


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

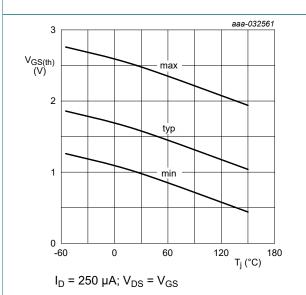
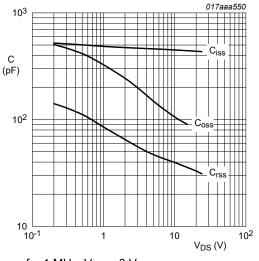


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

30 V, N-channel Trench MOSFET

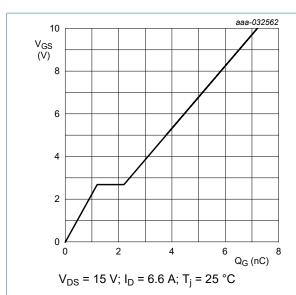


Fig. 14. Gate-source voltage as a function of gate charge; typical values

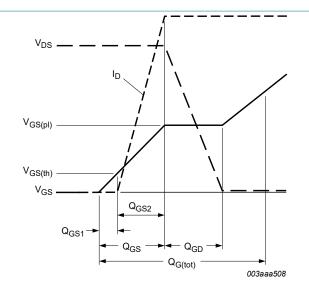


Fig. 15. Gate charge waveform definitions

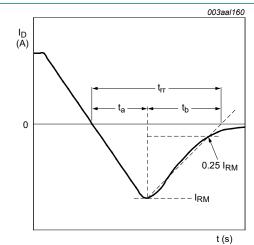


Fig. 16. Reverse recovery timing definition

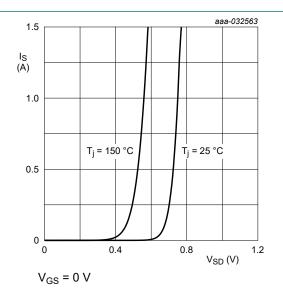
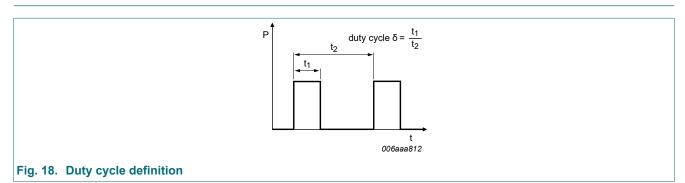


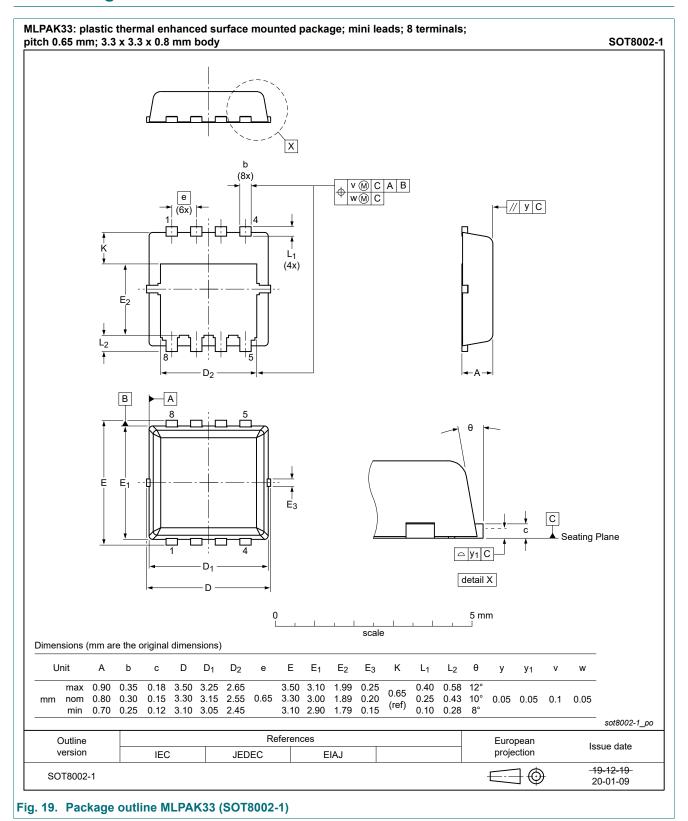
Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information



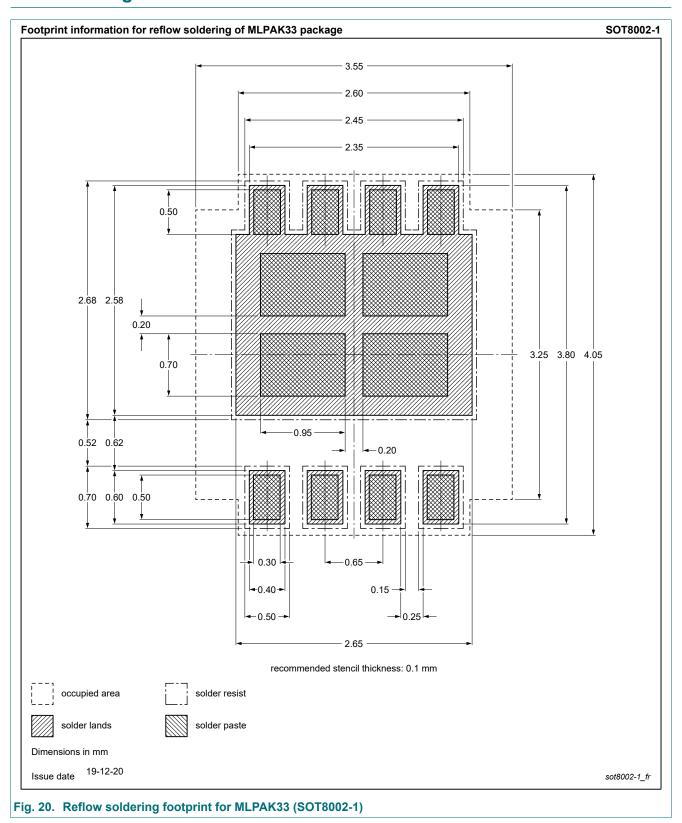
30 V, N-channel Trench MOSFET

12. Package outline



30 V, N-channel Trench MOSFET

13. Soldering



30 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PXN018-30QL v.1	20210105	Product data sheet	-	-

30 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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30 V, N-channel Trench MOSFET

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	Characteristics	6
11.	Test information	9
12.	Package outline	10
	Soldering	
14.	Revision history	12
	Legal information	
	-	

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